1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4032PX.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- Optimized switching time
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	30	V
I _C	collector current		-	-	4.7	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	10	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = 4 A;$ $I_B = 400 \text{ mA}$	[1] -	45	62.5	mΩ

^[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$



Product data sheet

2. Pinning information

Table 2. Pinning

	3		
Pin	Description	Simplified outline	Graphic symbol
1	emitter		
2	collector		2
3	base		3—
		3 2 1	sym042

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4032NX	SC-62	plastic surface-mounted package; 3 leads	SOT89		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS4032NX	*6H

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

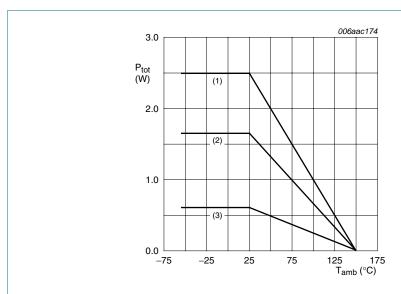
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	30	V
V_{CEO}	collector-emitter voltage	open base	-	30	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current		-	4.7	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	10	Α
I _B	base current		-	1	А

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

P_{tot} total power dissipation $T_{amb} \le 25 ^{\circ}C$ [1] - 600 mW	,	• • •		
and = 20 = 000 iiii	Min Max Unit	Conditions	Parameter	Symbol
[2] - 1650 mW	- 600 mW	$T_{amb} \le 25 ^{\circ}C$	total power dissipation	P _{tot}
	- 1650 mW			
3 - 2500 mW	- 2500 mW			
T _j junction temperature - 150 °C	- 150 °C		junction temperature	Tj
T _{amb} ambient temperature –55 +150 °C	–55 +150 °C		ambient temperature	T _{amb}
T _{stg} storage temperature –65 +150 °C	–65 +150 °C		storage temperature	T _{stg}

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	<u>[1]</u>	-	-	210	K/W
jun	junction to ambient		[2]	-	-	75	K/W
			[3]	-	-	50	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

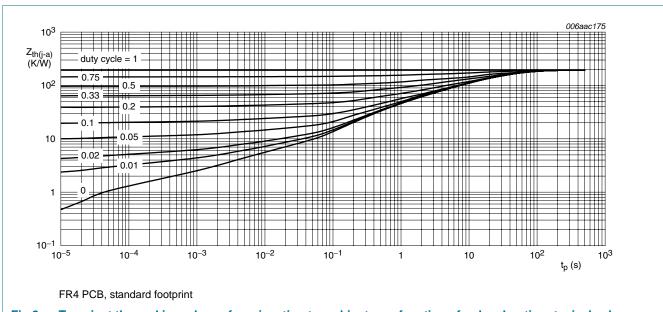
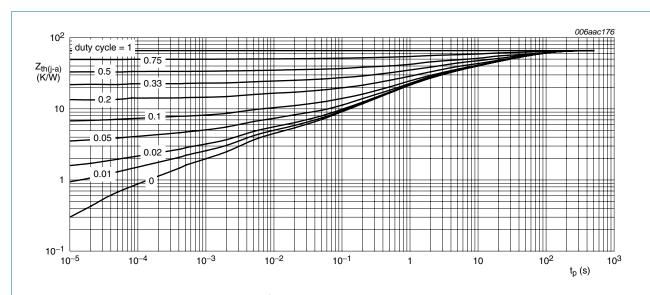
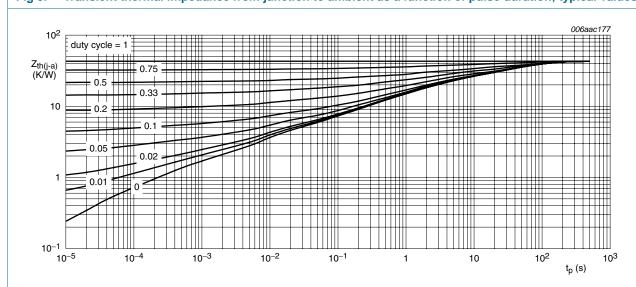


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

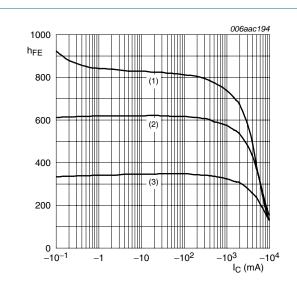
7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	50	μА
I _{CES}	collector-emitter cut-off current	$V_{CE} = 24 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V	[1]				
		$I_C = 500 \text{ mA}$		300	500	-	
		I _C = 1 A		300	500	-	
		I _C = 2 A		250	450	-	
		I _C = 4 A		200	350	-	
		I _C = 6 A		150	275	-	
V_{CEsat}	collector-emitter		[1]				
	saturation voltage	$I_C = 1 \text{ A}; I_B = 50 \text{ mA}$		-	90	125	mV
		$I_C = 1 \text{ A}; I_B = 10 \text{ mA}$		-	130	180	mV
		$I_C = 2 \text{ A}; I_B = 40 \text{ mA}$		-	150	210	mV
		I _C = 4 A; I _B = 400 mA		-	180	250	mV
	$I_C = 4 \text{ A}; I_B = 40 \text{ mA}$		-	250	375	mV	
		$I_C = 5.4 \text{ A}; I_B = 270 \text{ mA}$		-	240	340	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = 4 \text{ A}; I_B = 400 \text{ mA}$	[1]	-	45	62.5	mΩ
V_{BEsat}	base-emitter	$I_C = 1 A$; $I_B = 100 \text{ mA}$	<u>[1]</u>	-	0.75	0.9	V
	saturation voltage	$I_C = 4 \text{ A}; I_B = 400 \text{ mA}$	<u>[1]</u>	-	0.92	1.05	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	[1]	-	0.77	0.85	V
t _d	delay time	$V_{CC} = 12.5 \text{ V}; I_C = 1 \text{ A};$		-	35	-	ns
t _r	rise time	$I_{Bon} = 0.05 \text{ A};$		-	30	-	ns
t _{on}	turn-on time	$I_{Boff} = -0.05 \text{ A}$		-	65	-	ns
t _s	storage time			-	150	-	ns
t _f	fall time			-	65	-	ns
t _{off}	turn-off time			-	215	-	ns
f _T	transition frequency	$V_{CE} = 10 \text{ V};$ $I_{C} = 100 \text{ mA};$ $f = 100 \text{ MHz}$		-	145	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	65	-	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



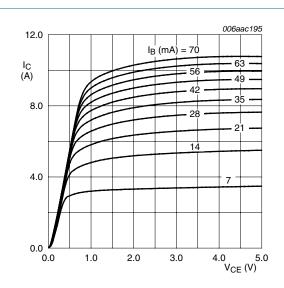
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

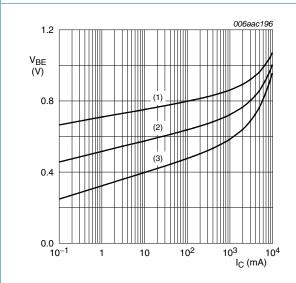
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 6. Collector current as a function of collector-emitter voltage; typical values



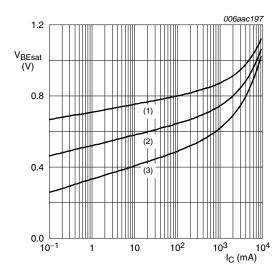
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

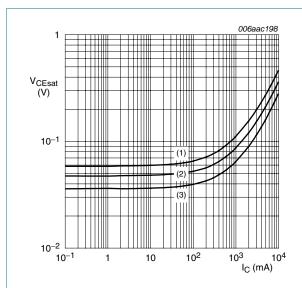
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values

30 V, 4.7 A NPN low V_{CEsat} (BISS) transistor



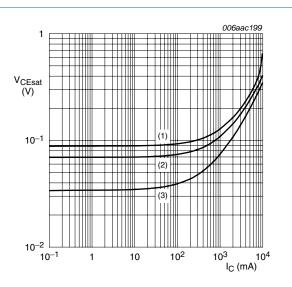
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



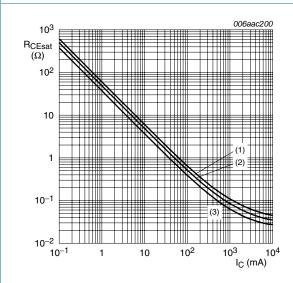
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



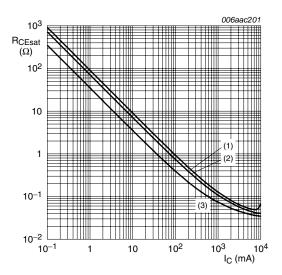
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



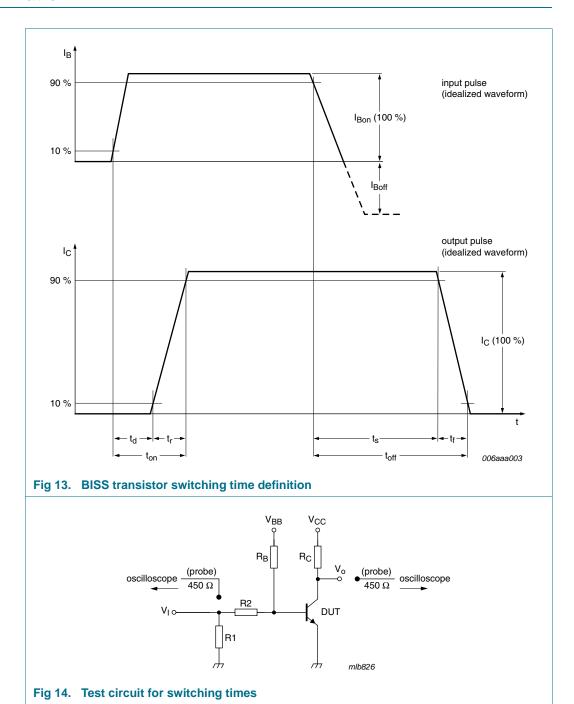
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

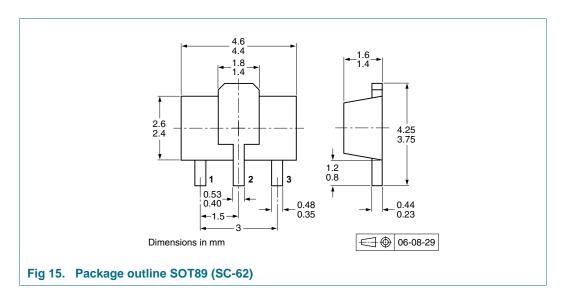
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

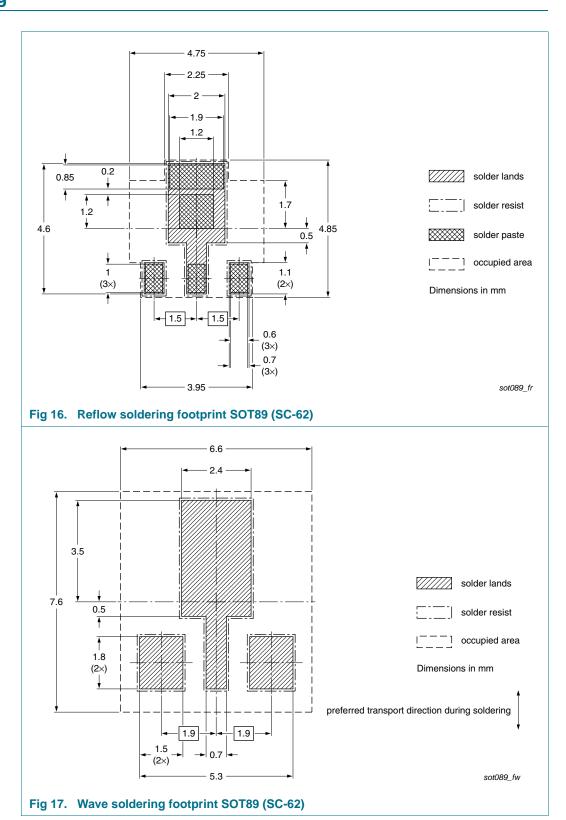
Type number	Package	Description		Packing quantity		
				3000	10000	
PBSS4032NX	SOT89	8 mm pitch, 12 mm tape and reel; T1	[2]	-115	-135	
		8 mm pitch, 12 mm tape and reel; T3	[3]	-120	-	

^[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T3: 90° rotated taping

11. Soldering



PBSS4032NX

30 V, 4.7 A NPN low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4032NX_1	20100401	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PBSS4032NX 1

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PBSS4032NX

30 V, 4.7 A NPN low V_{CEsat} (BISS) transistor

14. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: $\underline{\textbf{salesaddresses@nexperia.com}}$

15. Contents

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